

Silicon PNP transistor epitaxial type A5914

[Applications]

High speed switching
DC-DC convertor
Strobe flash

[Feature]

High DC gain $hFE= 200-500$ at $VCE= -2V, IC= -0.3A$
Low collector saturation voltage $VCE(sat)= -0.2V$ (Max.) at $IC= -1A, IB= -33mA$
High speed switching time $tf= 90ns$ (Typ.) at $VCC= -30V, IC= -1A, IB= -33mA$

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-50	V
Collector-emitter voltage	VCEO	-50	V
Emitter-base voltage	VEBO	-7	V
Collector current (DC)	IC	-2	A
Collector current (Pulse)	ICP	-3.5	A
Base current	IB	-0.2	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BVCEO	-50	-	-	V	IC= -10mA, IB= 0A
Collector cut-off current	ICBO	-	-	-100	nA	VCB= -50V, IE= 0A
Emitter cut-off current	IEBO	-	-	-100	nA	VEB= -7V, IC= 0A
DC current gain 1	hFE 1	200	-	500	-	VCE= -2V, IC= -0.3A
DC current gain 2	hFE 2	100	-	-	-	VCE= -2V, IC= -1A
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.2	V	IC= -1A, IB= -33mA
Base-emitter saturation voltage	VBE(sat)	-	-	-1.1	V	IC= -1A, IB= -33mA
Transition frequency	fT	-	180	-	MHz	VCE= -2V, IE= 0.3A
Collector output capacitance	Cob	-	20	-	pF	VCB= -10V, f = 1MHz, IE= 0A
Turn on time	ton	-	60	-	ns	VCC= -30V, IC= -1A -IB1= IB2= 33mA
Storage time	tstg	-	250	-	ns	
Fall time	tf	-	90	-	ns	

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

No. A5914-20070517

Fig.1 IC - VBE(on)
at VCE= -2V, Ta= 25C

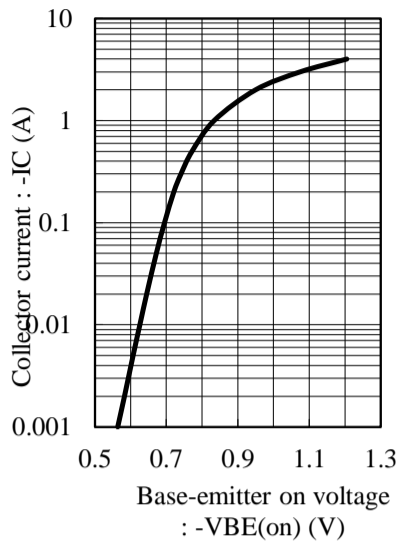


Fig.2 hFE - IC
at VCE= -2V, Ta= 25C

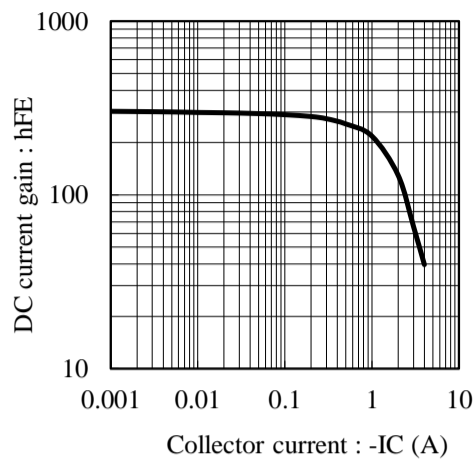


Fig.3 VCE(sat) - IC
at IC/IB= 30, Ta= 25C

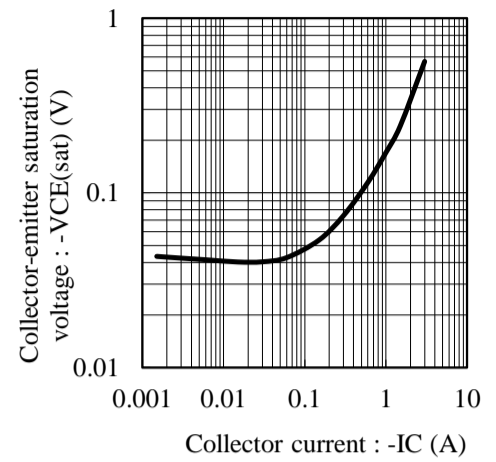


Fig.4 VBE(sat) - IC
at IC/IB= 30, Ta= 25C

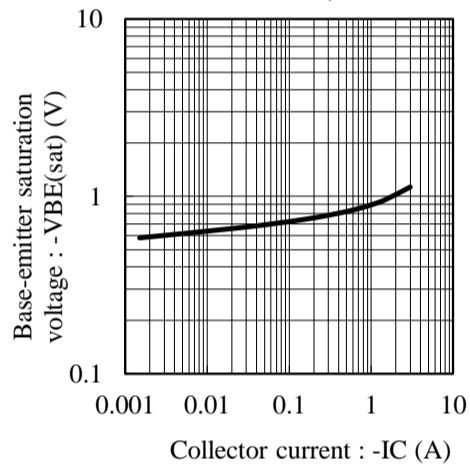


Fig.5 fT - IE
at VCE= -2V, Ta= 25C

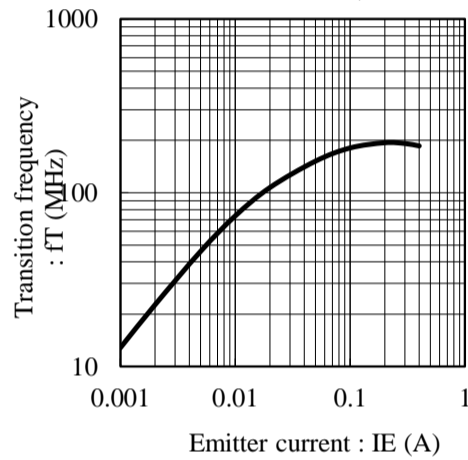


Fig.6 Cob - VCB
at f= 1MHz, Ta= 25C

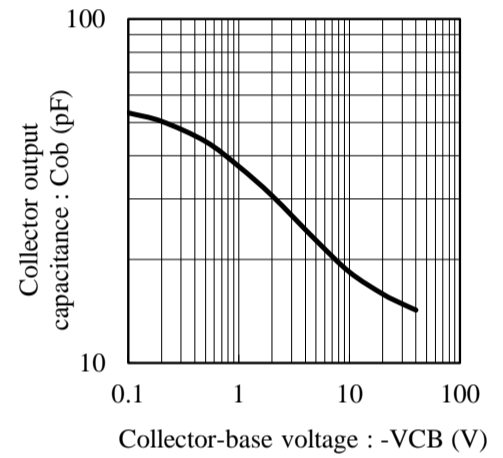


Fig.7 Cib - VEB
at f= 1MHz, Ta= 25C

